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The invention relates to the nanostructured materials production technology, in particular to methods for producing nanostructures by electrochemical machining.

The method, according to the invention, comprises making an electrical contact of a silver paste on an n-GaAs wafer with (111)B crystallographic orientation, installing the wafer on an O-ring in a Teflon cell and anodizing it in an electrolyte which contains a 1M HNO<sub>3</sub> solution at room temperature for 20 minutes, in potentiostatic mode with a voltage supply of 3.0...4.5 V.

Claims: 1

Fig.: 2